

What is claimed is:

1. A resist pattern forming method comprising the steps of:
  - forming a resist layer on a substrate by applying a non-chemically amplified resist onto the substrate;
  - exposing the resist layer;
  - baking the substrate subjected to the exposure at a temperature not lower than 90°C but not higher than 130°C; and
  - developing the baked substrate.
2. A resist pattern forming method as claimed in claim 1, wherein said step of baking the substrate includes baking the substrate at a baking temperature not lower than 100°C but not higher than 120°C, over a baking time period not shorter than 2 minutes but not longer than 60 minutes.
3. A resist pattern forming method as claimed in claim 1, wherein said step of baking the substrate includes baking the substrate at a baking temperature not lower than 90°C but lower than 100°C, over a baking time period not shorter than 10 minutes but not longer than 60 minutes.
4. A resist pattern forming method as claimed in claim 1, wherein said step of baking the substrate includes baking the substrate at a baking temperature higher than 120°C but not higher than 130°C, over a baking time period not shorter than 2 minutes but not longer than 30 minutes.
5. A resist pattern forming system comprising:
  - a resist layer forming apparatus that forms a resist layer on a substrate by applying a non-chemically amplified resist onto the substrate;

an exposure apparatus that exposes the resist layer formed on the substrate;

a baking apparatus that bakes the substrate exposed by said exposure apparatus, at a temperature not lower than 90°C but not higher than 130°C; and

a developing apparatus that develops the substrate baked by said baking apparatus.

6. A resist pattern forming system as claimed in claim 5, wherein said baking apparatus bakes the substrate at a baking temperature not lower than 100°C but not higher than 120°C, over a baking time period not shorter than 2 minutes but not longer than 60 minutes.

7. A resist pattern forming system as claimed in claim 5, wherein said baking apparatus bakes the substrate at a baking temperature not lower than 90°C but lower than 100°C, over a baking time period not shorter than 10 minutes but not longer than 60 minutes.

8. A resist pattern forming system as claimed in claim 5, wherein said baking apparatus bakes the substrate at a baking temperature higher than 120°C but not higher than 130°C, over a baking time period not shorter than 2 minutes but not longer than 30 minutes.